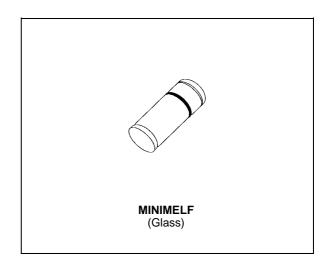
# TMMBAT 47 TMMBAT 48

## SMALL SIGNAL SCHOTTKY DIODES



#### **DESCRIPTION**

General purpose, metal to silicon diodes featuring very low turn-on voltage and fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

## **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		TMMBAT47	TMMBAT48	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		20	40	V
IF	Forward Continuous Current	T <sub>I</sub> = 25 °C 350		50	mA
I <sub>FRM</sub>	Repetitive Peak Fordward Current	$\begin{array}{l} t_p \leq 1s \\ \delta \leq 0.5 \end{array}$	1		Α
I <sub>FSM</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms	7.5		Α
		t <sub>p</sub> = 1s	1.5		
P <sub>tot</sub>	Power Dissipation	T <sub>I</sub> = 25 °C	330		mW
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125		°C °C
$T_L$	Maximum Temperature for Soldering during 15s		260		°C

#### THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R <sub>th(j-l)</sub>	Junction-leads	300	°C/W

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### **ELECTRICAL CHARACTERISTICS**

### STATIC CHARACTERISTICS

Symbol		Test Conditions		Min.	Тур.	Max.	Unit
$V_{BR}$	T <sub>j</sub> = 25°C	$I_R = 10\mu A$	TMMBAT47	20			V
	T <sub>j</sub> = 25°C	$I_R = 25\mu A$	TMMBAT48	40			
V <sub>F</sub> *	T <sub>j</sub> = 25°C	$I_F = 0.1 \text{mA}$	All Types			0.25	V
	T <sub>j</sub> = 25°C	$I_F = 1mA$				0.3	
	T <sub>j</sub> = 25°C	$I_F = 10mA$				0.4	
	T <sub>j</sub> = 25°C	$I_F = 30 \text{mA}$	TMMBAT47			0.5	
	T <sub>j</sub> = 25°C	$I_F = 150 \text{mA}$				0.8	
	T <sub>j</sub> = 25°C	$I_F = 300 \text{mA}$				1	
	T <sub>j</sub> = 25°C	$I_F = 50 \text{mA}$	TMMBAT48			0.5	
	T <sub>j</sub> = 25°C	$I_F = 200 \text{mA}$				0.75	
	T <sub>j</sub> = 25°C	$I_F = 500 \text{mA}$				0.9	
I <sub>R</sub> *	T <sub>j</sub> = 25°C	$V_{R} = 1.5V$	All Types			1	μΑ
	$T_j = 60^{\circ}C$					10	
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 10V	TMMBAT47			4	
	T <sub>j</sub> = 60°C					20	
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 20V				10	
	T <sub>j</sub> = 60°C					30	
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 10V	TMMBAT48			2	
	T <sub>j</sub> = 60°C					15	
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 20V				5	
	T <sub>j</sub> = 60°C					25	
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 40V				25	
	T <sub>j</sub> = 60°C					50	

## DYNAMIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
С	$T_j = 25$ °C $V_R = 0V$ $f = 1MHz$		20		рF
	$T_j = 25$ °C $V_R = 1V$		12		
t <sub>rr</sub>	$T_{j} = 25^{\circ}C$ $I_{F} = 10mA$ $V_{R} = 1V$ $i_{rr} = 1mA$ $R_{L} = 10$	ΟΩ	10		ns

<sup>\*</sup> Pulse test:  $t_p \le 300 \mu s$   $\delta < 2\%$ .



Figure 1. Forward current versus forward voltage at different temperatures (typical values).

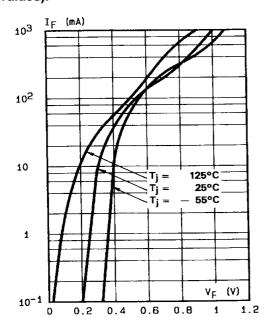


Figure 2. Forward current versus forward voltage (typical values).

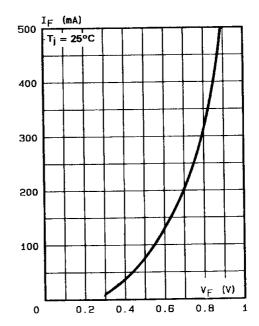


Figure 3. Reverse current versus junction temperature.

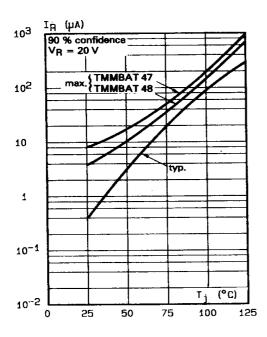
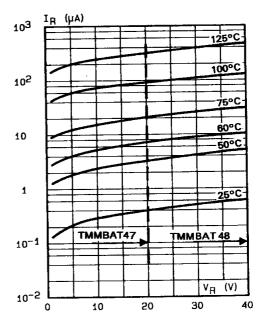
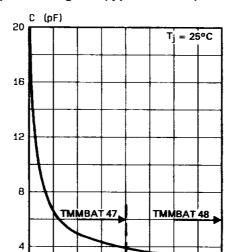


Figure 4. Reverse current versus continuous reverse voltage (typical values).





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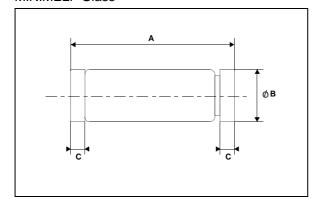
v<sub>A</sub> (v)

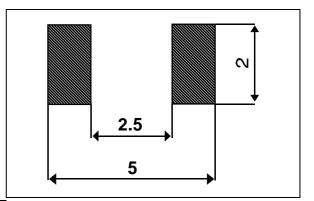
Figure 5. Capacitance C versus reverse applied voltage  $V_{\mbox{\scriptsize R}}$  (typical values).

#### **PACKAGE MECHANICAL DATA**

#### **FOOT PRINT DIMENSIONS** (Millimeter)

#### **MINIMELF Glass**





	DIMENSIONS				
REF.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	3.3	3.6	0.130	0.142	
В	1.59	1.62	0.063	0.064	
С	0.4	0.5	0.016	0.020	

Marking: ring at cathode end. Weight: 0.05g

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